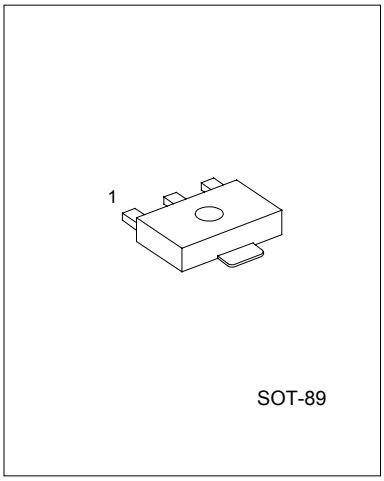
UTC 2SB766A PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY OUTPUT AMPLIFICATION



1:EMITTER 2:COLLECTOR 3:BASE

FEATURES

*Large collector power dissipation Pc.
*Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	Ic	-1	A
Peak Collector Current	Icp	-1.5	A
Collector Power Dissipation	Pc*	1	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

*Printed circuit board :Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion.

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Voltage	V_{CBO}	Ic= -10 μA ,I_E=0	-60			V
Collector Emitter Voltage	V_{CEO}	Ic= -2mA ,I_B= 0	-50			V
Emitter Base Voltage	V_{EBO}	I_E= -10 μA, I_C=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}= -20V,I_E=0			-0.1	μA
DC Current Transfer Ratio	h_{FE1}	V_{CE}= -10V,Ic= -500mA *	85		340	
	h_{FE2}	V_{CE}= -5V,Ic= -1A *	50			
Collector-Emitter Saturation Voltage	V_{CE}(sat)	Ic = -500mA,I_B =-50mA*		-0.2	-0.4	V
Base-Emitter Saturation Voltage	V_{BE}(sat)	Ic = -500mA,I_B =-50mA*		-0.85	-1.2	V
Transition Frequency	f_T	V_{CB}= -10V, I_E= 50 mA, f=200MHz		200		MHz
Output Capacitance	Cob	V_{CB}= -10V, I_E= 0, f=1MHz		20	30	pF

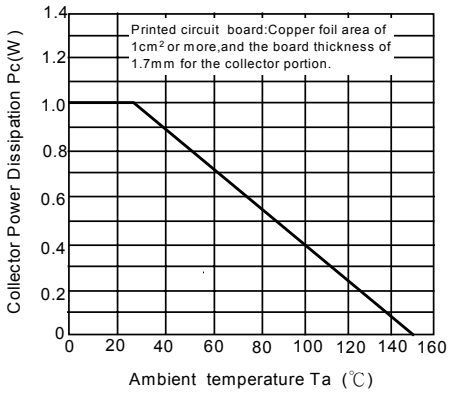
*Pulse measurement

CLASSIFICATION OF hFE1

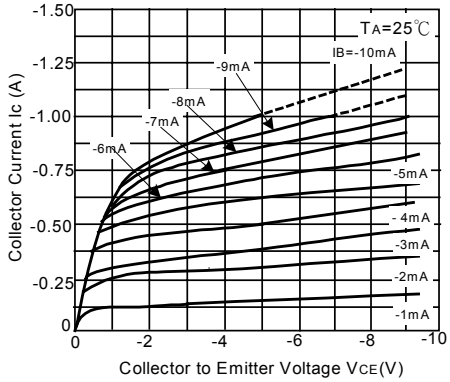
RANK	Q	R	S
RANGE	85-170	120-240	170-340

ELECTRICAL CHARACTERISTICS CURVES

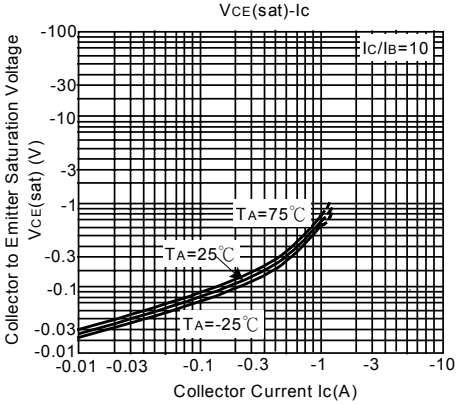
Pc-Ta



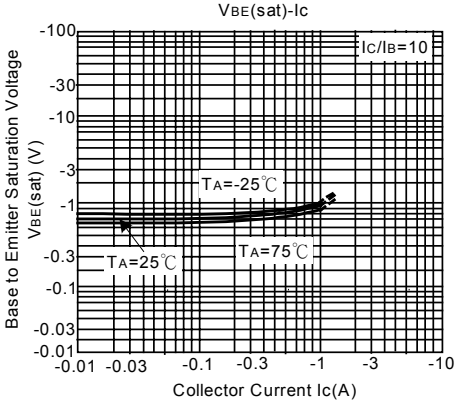
Ic-VCE



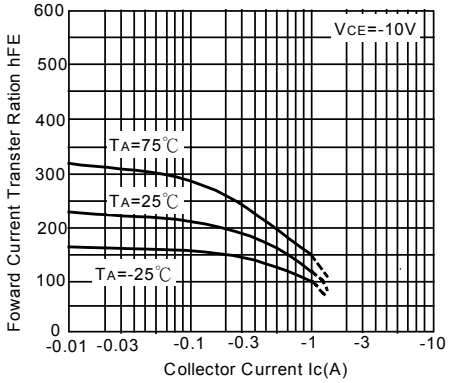
VCE(sat)-Ic



VBE(sat)-Ic



hFE-Ic



fT-IE